

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	ASAKAWA-KOJI and HOTTA-YASUYUKI and MATAKE-SHIGERU and HIRAOKA-TOSHIRO	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/09 09:41
L2	1	2001jp-0170018.ap,prai. 2001jp-0295461.ap,prai.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/09 09:50
L3	1	2003-203074.NRAN.	DERWENT	OR	OFF	2004/11/09 09:51
L4	17	"5731073".uref. "5910354".uref.	US-PGPUB; USPAT	OR	OFF	2004/11/09 09:53
L5	0	"6649516".URPN.	USPAT	OR	OFF	2004/11/09 10:02
L6	0	"6608757".URPN.	USPAT	OR	OFF	2004/11/09 10:02
L7	16	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (expos\$4 with beam)	US-PGPUB; USPAT	OR	ON	2004/11/09 10:02
L8	377	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (via feedthrough throughhole wiring interconnect trace)	US-PGPUB; USPAT	OR	ON	2004/11/09 10:07
L9	14	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (via feedthrough throughhole wiring interconnect trace)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 10:36
L10	23	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (438/638.ccls. 29/829.ccls. 29/846. ccls. 29/880.ccls. 174/262.ccls. 200/264.ccls. 361/748.ccls.)	US-PGPUB; USPAT	OR	ON	2004/11/09 10:40
L11	274	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (via feedthrough throughhole) and (wiring interconnect trace)	US-PGPUB; USPAT	OR	ON	2004/11/09 10:43

L12	297	(438/638.ccls. 29/829.ccls. 29/846.ccls. 29/880.ccls. 174/262.ccls. 200/264.ccls. 361/748.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)))	US-PGPUB; USPAT	OR	ON	2004/11/09 10:53
L13	40	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.) and ((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))	US-PGPUB; USPAT	OR	ON	2004/11/09 11:30
L14	101	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (mask photomask)	US-PGPUB; USPAT	OR	ON	2004/11/09 11:23
L16	14	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)) same (mask photomask)	US-PGPUB; USPAT	OR	ON	2004/11/09 11:32
L17	185	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)) and (mask photomask)	US-PGPUB; USPAT	OR	ON	2004/11/09 11:34
L18	102	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same (conduct\$4 metal infiltrat\$4 impregnat\$4)) and (mask photomask)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 11:42
L19	47	430/5.ccls. and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)))	US-PGPUB; USPAT	OR	ON	2004/11/09 11:49

L21	2677	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)) ((mask photomask) with (aperture via opening hole channel)))	US-PGPUB; USPAT	OR	ON	2004/11/09 12:00
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